

NEW ENGLAND SEMICONDUCTOR

BIPOLAR NPN TRANSISTOR TO-66

PACKAGE	DEVICE TYPE	V _{CEO} (sus) VOLTS	I _C (max) AMPS	h _{FE} @ I _C / V _{CE} (min/max @ A/V)	V _{CE(sat)} @ I _C /I _B (V @ A/A)	P _D * WATTS	f _T (MHz)
NPN TO-66 	2N3054A	55	4	25-100@.5/4	1@.5/.05	75	3
	2N3583	250 ^h	1	40-200@.5/10	5@1/.125	35	10
	2N3584^	300 ^h	5	25-100@1/10	.75@1/.125	35	10
	2N3585^	400 ^h	5	25-100@1/10	.75@1/.125	35	10
	2N3738	225	.25	40-200@.1/10	2.5@.25/.025	20	10
	2N3739^	300	.25	40-200@.1/10	2.5@.25/.025	20	10
	2N3766^	60	1	40-160@.5/5	1@.5/.05	20	10
	2N3767^	80	1	40-160@.5/5	12.5/.05	20	10
	2N3878	50	4	40-200@.5/2	2@4/.4	35	40
	2N3879^	75	7	12-100@4/2	1.2@4/.4	35	40
	2N4911	60	1	20-100@.5/1	.6@1/.1	25	3
	2N4912	80	1	20-100@.5/1	.6@1/.1	25	3
	2N5660^	200	1	40-120@.5/5	.4@1/.1	2.0	20
	2N5661^	300	1	25-75@.5/5	.4@1/.1	2.0	20
	2N5664^	200	3	40-120@1/5	.4@3/.3	2.5	20
	2N5665^	300	3	25-75@1/5	.4@3/.6	2.5	20
	2N6315	60	7	20-100@2.5/4	1@4/.4	90	4
	2N6316	80	7	20-100@2.5/4	1@4/.4	90	4
	2N6372	40	6	20-100@3/4	1@3/.3	40	4
	2N6373	60	6	20-100@2.5/4	1@2.5/.25	40	4
	2N6374	80	6	20-100@2/4	1@2/.2	40	4

* T_C = 25°C

^h V_{CER}

^Available in JAN, JANTX, JANTXV